# MSKSEMI















**ESD** 

TVS

TSS

MOV

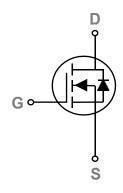
GDT

**PLED** 

# Broduct data sheet







BVDSS	RDSON	ID
60V	1.7Ω	200mA

#### **Features**

- $60V,200mA, RDS(ON) = 1.7\Omega@VGS = 10V$
- Fast switching
- Green Device Available

### **Applications**

- Notebook
- Smartphone
- Battery Protection
- Hand-held Instruments

#### Absolute Maximum Ratings Tc=25°C unless otherwise noted

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	60	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
1_	Drain Current – Continuous (T <sub>A</sub> =25°C)	200	mA
ID	Drain Current – Continuous (T <sub>A</sub> =70°C)	160	mA
I <sub>DM</sub>	Drain Current – Pulsed <sup>1</sup>	800	mA
D-	Power Dissipation (T <sub>A</sub> =25°C)	156	mW
PD	Power Dissipation – Derate above 25°C	1.25	mW/°C
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C

#### **Thermal Characteristics**

Symbol	Parameter	Тур.	Max.	Unit
Reja	Thermal Resistance Junction to ambient		800	°C/W



### **Electrical Characteristics** (T<sub>J</sub>=25 °C, unless otherwise noted)

#### **Off Characteristics**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =250uA	60			V
1	Drain Source Lookage Current	V <sub>DS</sub> =60V , V <sub>GS</sub> =0V , T <sub>J</sub> =25°C			10	nA
IDSS	Drain-Source Leakage Current	V <sub>DS</sub> =48V , V <sub>GS</sub> =0V , T <sub>J</sub> =125°C			100	nA
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V , V <sub>DS</sub> =0V			±100	nA

#### **On Characteristics**

R <sub>DS(ON)</sub> Static Drain-Source On-Resistance	V <sub>GS</sub> =10V , I <sub>D</sub> =0.15A		1.6	3	Ω	
	V <sub>GS</sub> =4.5V , I <sub>D</sub> =0.1A		1.7	4		
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.0	2	3.0	V
gfs	Forward Transconductance	V <sub>DS</sub> =10V , I <sub>D</sub> =0.1A		0.3		S

#### **Dynamic and switching Characteristics**

•				
$Q_g$	Total Gate Charge <sup>2, 3</sup>		 2	
$Q_{gs}$	Gate-Source Charge <sup>2, 3</sup>	V <sub>DS</sub> =30V , V <sub>GS</sub> =10V , I <sub>D</sub> =0.1A	 0.9	nC
$Q_{gd}$	Gate-Drain Charge <sup>2, 3</sup>		 0.4	
T <sub>d(on)</sub>	Turn-On Delay Time <sup>2, 3</sup>		 3	
Tr	Rise Time <sup>2, 3</sup>	$V_{DD}$ =30V , $V_{GS}$ =10V , $R_{G}$ =6 $\Omega$	 5	no
T <sub>d(off)</sub>	Turn-Off Delay Time <sup>2, 3</sup>	I <sub>D</sub> =0.1A	 14	ns
Tf	Fall Time <sup>2, 3</sup>		 9	
Ciss	Input Capacitance		 25	
Coss	Output Capacitance	V <sub>DS</sub> =30V , V <sub>GS</sub> =0V , F=1MHz	 15	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		 6.8	

#### **Drain-Source Diode Characteristics and Maximum Ratings**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current	V-=V-=0V Force Current			200	mA
Ism	Pulsed Source Current	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current			400	mA
VsD	Diode Forward Voltage	V <sub>GS</sub> =0V , I <sub>S</sub> =0.1A , T <sub>J</sub> =25°C			1	V
Trr	Reverse Recovery Time V <sub>R</sub> =50V, Is=0.1A ,			18		ns
Q <sub>rr</sub>	Reverse Recovery Charge	dl/dt=100A/µs, Tյ=25°C		6		nC

- 1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
- $\begin{array}{ll} 2. & \text{The data tested by pulsed , pulse width} \leq 300 us \text{ , duty cycle} \leq 2\%. \\ 3. & \text{Essentially independent of operating temperature.} \end{array}$



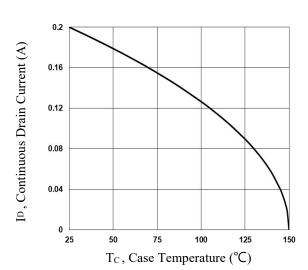


Fig.1 Continuous Drain Current vs.  $T_c$ 

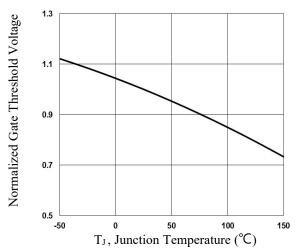


Fig.3 Normalized Vth vs. TJ

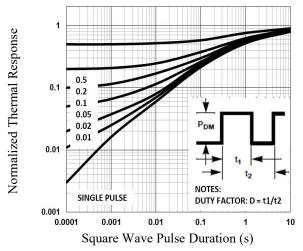


Fig.5 Normalized Transient Response

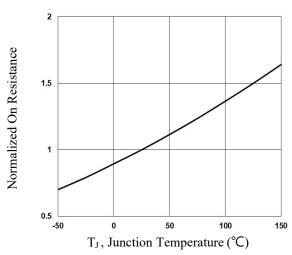


Fig.2 Normalized RDSON vs. T<sub>J</sub>

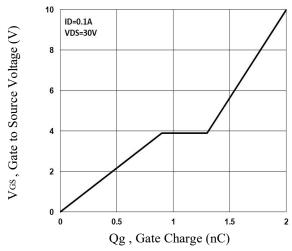


Fig.4 Gate Charge Waveform

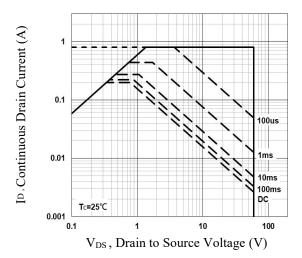
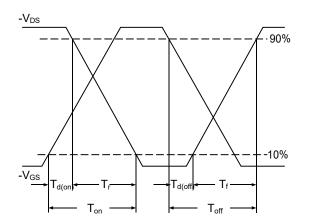


Fig.6 Maximum Safe Operation Area







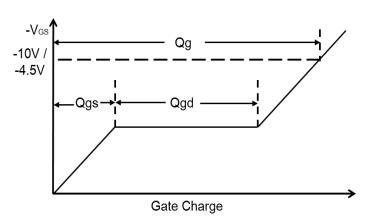
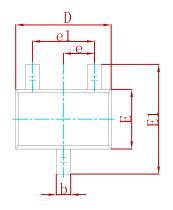
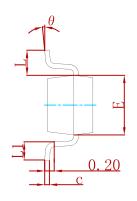


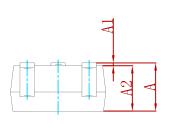
Fig.8 Gate Charge Waveform



#### **PACKAGE MECHANICAL DATA**

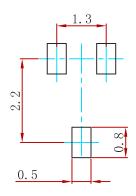






Cumbal	Dimensions	Dimensions In Millimeters		s In Inches
Symbol	Min	Max	Min	Max
Α	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
С	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
е	0.650 TYP		0.026	6 TYP
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.02	I REF
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

# Suggested Pad Layout



#### Note:

- 1. Controlling dimension:in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.

#### **REEL SPECIFICATION**

P/N	PKG	QTY
2N7002W	SOT-323	3000



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DMN61D9UWQ-13 US6M2GTR DMN31D5UDJ-7 DMP22D4UFO-7B IPS60R3K4CEAKMA1 DMN1006UCA6-7 DMN16M9UCA6-7
STF5N65M6 IRF40H233XTMA1 STU5N65M6 DMN6022SSD-13 DMN13M9UCA6-7 DMTH10H4M6SPS-13 IPS60R360PFD7SAKMA1
DMN2990UFB-7B SSM3K35CT,L3F IPLK60R1K0PFD7ATMA1 2N7002W-G MCAC30N06Y-TP IPWS65R035CFD7AXKSA1
MCQ7328-TP SSM3J143TU,LXHF DMN12M3UCA6-7 PJMF280N65E1\_T0\_00201 PJMF380N65E1\_T0\_00201
PJMF280N60E1\_T0\_00201 PJMF600N65E1\_T0\_00201 PJMF900N65E1\_T0\_00201